

PATENT  
790001-2037**AMENDMENT TO THE SPECIFICATION**

On page 4, lines 20-27, please substitute the following amended paragraph below:

-----A semiconductor memory device according to an aspect of the present invention, comprises: a semiconductor substrate; a flat-plate-shaped cavity made in the semiconductor substrate; and an element isolating region formed in the surface of the semiconductor substrate and located at the sides of the cavity, the cavity being wider than an element region provided on the cavity, wherein the element isolating region is less deep than the cavity and deeper than the element region.-----